# 2SB1435

## Silicon PNP epitaxial planar type

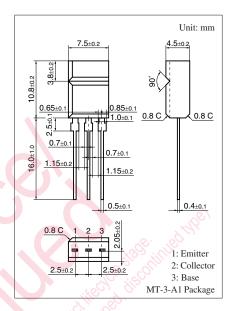
### For low-frequency output amplification

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- Large collector current I<sub>C</sub>
- Allowing automatic insertion with radial taping

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	V <sub>CBO</sub> -50		
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V	
Collector current	$I_C$	-2	A	
Peak collector current	$I_{CP}$	-3	A	
Collector power dissipation	P <sub>C</sub>	1.5	W	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



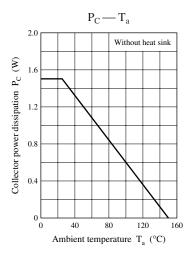
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

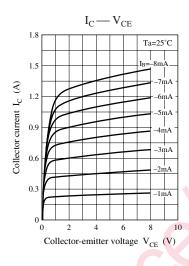
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emiter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \; \mu \text{A},  I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$	-50			V
Emiter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A},  I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -2 \text{ V}, I_{C} = -200 \text{ mA}$	120		340	_
	h <sub>FE2</sub>	$V_{CE} = -2 \text{ V}, I_{C} = -1 \text{ A}$	60			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		- 0.2	- 0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		- 0.85	-1.20	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45	60	pF
(Common base, input open circuited)						

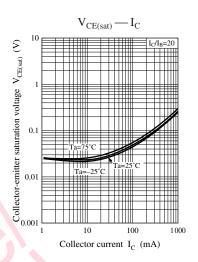
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

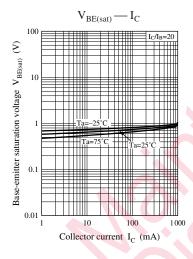
#### 2. \*: Rank classification

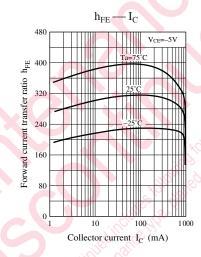
Rank	R	S
h <sub>FE1</sub>	120 to 240	170 to 340

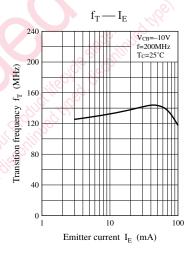


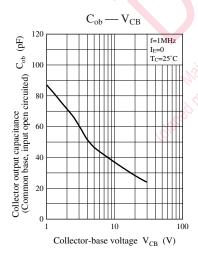


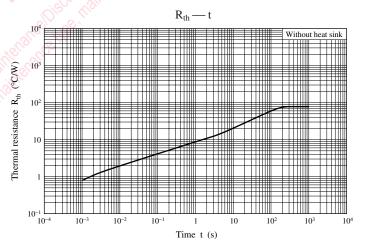












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